

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	0	interconnect and copper and via and trench and (organic adj monolayer) and seal\$3 and (remov\$4 near3 monolayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 11:42
2	BRS	0	interconnect and copper and via and trench and (organic adj monolayer) and seal\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 11:39
3	BRS	0	interconnect and copper and via and trench and (organic adj monolayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 11:40
4	BRS	135	organic adj monolayer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:21
5	BRS	9	interconnect and (organic adj monolayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 11:40
6	BRS	5	interconnect and copper and via and trench and (monolayer) and seal\$3 and (remov\$4 near3 monolayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:06
7	BRS	1	438/\$.ccls. and interconnect and chemisorb\$3 and desorb\$3 and organic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 11:55
8	BRS	14	interconnect and chemisorb\$3 and desorb\$3 and organic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 11:57
9	BRS	219	chemisorb\$3 and desorb\$3 and organic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:55
10	BRS	4	chemisorb\$3 and desorb\$3 and damascene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:08
11	BRS	4	chemisorb\$3 and desorb\$3 and organic and damascene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 11:59
12	BRS	7	interconnect and via and trench and (monolayer) and seal\$3 and (remov\$4 near3 monolayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:15
13	BRS	706	remov\$4 adj3 monolayer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:11
14	BRS	119	chemisorb\$3 and desorb\$3 and monolayer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:08
15	BRS	6	chemisorb\$3 and desorb\$3 and monolayer and interconnect	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:08
16	BRS	0	remov\$4 adj3 organic adj3 monolayer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:11

	Type	Hits	Search Text	DBs	Time Stamp
17	BRS	27	portion with (remov\$4 adj3 monolayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:21
18	BRS	6	damascene and (monolayer) and seal\$3 and (remov\$4 adj3 monolayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 10:26
19	BRS	0	(organic adj monolayer) with remov\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:22
20	BRS	2	expose with (remov\$4 adj3 monolayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:22
21	BRS	2	(organic adj monolayer) same remov\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:22
22	BRS	3	exposing with (remov\$4 adj3 monolayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 10:14
23	BRS	130	chemisorb\$3 same desorb\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:58
24	BRS	54	chemisorb\$3 same desorb\$3 and monolayer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 09:59
25	BRS	28	chemisorb\$3 same desorb\$3 same monolayer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 10:00
26	BRS	0	thermal with (remov\$4 adj3 monolayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 10:16
27	BRS	0	oxidation with (remov\$4 adj3 monolayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 10:16
28	BRS	4	oxidation same (remov\$4 adj3 monolayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 10:17
29	BRS	7	thermal same (remov\$4 adj3 monolayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 10:19
30	BRS	2	thermal same (remov\$4 adj3 SAM)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 10:19
31	BRS	23	damascene and (remov\$4 adj3 monolayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 10:27
32	BRS	885	438/618.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 16:18
33	BRS	1783	438/637.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 16:18

	Type	Hits	Search Text	DBs	Time Stamp
34	BRS	1163	438/643.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 16:18
35	BRS	1420	438/680.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 16:18
36	BRS	927	438/778.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 16:18
37	BRS	1378	438/780.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 16:18
38	BRS	368	438/781.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 16:18

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 Time: 11:43:44


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## Inventor Name Search Result

Your Search was:

Last Name = GRACIAS

First Name = DAVID

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<a href="#"><u>60371532</u></a>	Not Issued	159	04/10/2002	METHOD OF SELF-ASSEMBLY AND SELF-ASSEMBLED STRUCTURES	GRACIAS, DAVID H.
<a href="#"><u>60347472</u></a>	Not Issued	159	01/11/2002	SELF-ASSEMBLED THREE-DIMENSIONAL STRUCTURES AND METHOD OF MAKING	GRACIAS, DAVID H.
<a href="#"><u>60226105</u></a>	Not Issued	159	08/17/2000	SELF-ASSEMBLED ELECTRICAL NETWORKS	GRACIAS, DAVID H.
<a href="#"><u>60219570</u></a>	Not Issued	159	07/20/2000	FORMING ELECTRICAL NETWORKS IN THREE DIMENSIONS BY SELF-ASSEMBLY	GRACIAS, DAVID H.
<a href="#"><u>10628297</u></a>	Not Issued	030	07/25/2003	PROTECTING METAL CONDUCTORS WITH SACRIFICIAL ORGANIC MONOLAYERS	GRACIAS, DAVID H.
<a href="#"><u>10439975</u></a>	Not Issued	030	05/16/2003	METHOD TO REDUCE THE COPPER LINE ROUGHNESS FOR INCREASED ELECTRICAL CONDUCTIVITY OF NARROW INTERCONNECTS (<100NM)	GRACIAS, DAVID H.
<a href="#"><u>10422432</u></a>	Not Issued	030	04/24/2003	FORMING THIN HARD MASK OVER AIR GAP OR POROUS DIELECTRIC	GRACIAS, DAVID H.
<a href="#"><u>10413919</u></a>	Not Issued	041	04/14/2003	METHOD TO INCREASE ELECTROMIGRATION RESISTANCE OF COPPER USING SELF-ASSEMBLED ORGANIC THIOLATE MONOLAYERS	GRACIAS, DAVID H.
<a href="#"><u>10360042</u></a>	Not Issued	030	02/06/2003	FABRICATING STACKED CHIPS USING FLUIDIC TEMPLATED-ASSEMBLY	GRACIAS, DAVID

<a href="#"><u>10306066</u></a>	Not Issued	030	11/27/2002	REDUCING LINE TO LINE CAPACITANCE USING ORIENTED DIELECTRIC FILMS	GRACIAS, DAVID
<a href="#"><u>10302073</u></a>	Not Issued	041	11/21/2002	SELECTIVELY CONVERTED INTER-LAYER DIELECTRIC	GRACIAS, DAVID H.
<a href="#"><u>10268132</u></a>	Not Issued	030	10/09/2002	REPLENISHMENT OF SURFACE CARBON AND SURFACE PASSIVATION OF LOW-K POROUS SILICON-BASED DIELECTRIC MATERIALS	GRACIAS, DAVID H.
<a href="#"><u>10209700</u></a>	Not Issued	071	08/01/2002	ADHESION OF CARBON DOPED OXIDES BY SILANIZATION	GRACIAS, DAVID H.
<a href="#"><u>10166150</u></a>	<a href="#"><u>6620741</u></a>	150	06/10/2002	METHOD FOR CONTROLLING ETCH BIAS OF CARBON DOPED OXIDE FILMS	GRACIAS, DAVID H.
<a href="#"><u>09909420</u></a>	Not Issued	083	07/19/2001	SELF-ASSEMBLED ELECTRICAL NETWORKS	GRACIAS, DAVID H.

Inventor Search Completed: No Records to Display.

<b>Search Another:</b>	<b>Last Name</b>	<b>First Name</b>
<b>Inventor</b>	<input type="text" value="GRACIAS"/>	<input type="text" value="DAVID"/>
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**Inventor Name Search Result**

Your Search was:

Last Name = KLOSTER

First Name = GRANT

<b>Application#</b>	<b>Patent#</b>	<b>Status</b>	<b>Date Filed</b>	<b>Title</b>	<b>Inventor Name 29</b>
10728616	Not Issued	020	12/05/2003	METHOD OF FORMING A STACKED DEVICE FILLER	KLOSTER, GRANT M.
<u>10683202</u>	Not Issued	030	10/09/2003	DEPOSITION OF DIFFUSION BARRIER	KLOSTER, GRANT
10631508	Not Issued	030	07/31/2003	METHOD OF BONDING SEMICONDUCTOR DEVICES	KLOSTER, GRANT
<u>10628297</u>	Not Issued	030	07/25/2003	PROTECTING METAL CONDUCTORS WITH SACRIFICIAL ORGANIC MONOLAYERS	KLOSTER, GRANT
10627838	Not Issued	020	07/25/2003	SEALING POROUS DIELECTRICS WITH SILANE COUPLING REAGENTS	KLOSTER, GRANT
<u>10600203</u>	Not Issued	071	06/20/2003	METHOD OF FORMING A STACKED DEVICE FILLER	KLOSTER, GRANT M.
<u>10455934</u>	Not Issued	020	06/06/2003	STACKED DEVICE UNDERFILL AND A METHOD OF FABRICATION	KLOSTER, GRANT M.
<u>10435704</u>	Not Issued	041	05/09/2003	METHOD FOR IMPROVING NUCLEATION AND ADHESION OF CVD AND ALD FILMS DEPOSITED ONTO LOW-DIELECTRIC-CONSTANT DIELECTRICS	KLOSTER, GRANT M.
10422432	Not Issued	030	04/24/2003	FORMING THIN HARD MASK OVER AIR GAP OR POROUS DIELECTRIC	KLOSTER, GRANT M.
<u>10395447</u>	Not Issued	092	03/24/2003	FORMING A POROUS DIELECTRIC LAYER	KLOSTER, GRANT M.
<u>10394104</u>	Not Issued	041	03/21/2003	FORMING A DIELECTRIC LAYER USING POROGENS	KLOSTER, GRANT M.
<u>10377061</u>	Not Issued	030	02/28/2003	FORMING A DIELECTRIC LAYER USING A	KLOSTER, GRANT M.

HYDROCARBON-CONTAINING PRECURSOR					
<a href="#"><u>10369931</u></a>	Not Issued	020	02/18/2003	BONDING A METAL COMPONENT TO A LOW-K DIELECTRIC MATERIAL	KLOSTER, GRANT M.
<a href="#"><u>10328806</u></a>	Not Issued	071	12/23/2002	METHOD OF MAKING SEMICONDUCTOR DEVICES USING CARBON NITRIDE, A LOW-DIELECTRIC-CONSTANT HARD MASK AND/OR ETCH STOP	KLOSTER, GRANT
<a href="#"><u>10302073</u></a>	Not Issued	041	11/21/2002	SELECTIVELY CONVERTED INTER-LAYER DIELECTRIC	KLOSTER, GRANT M.
<a href="#"><u>10301957</u></a>	Not Issued	041	11/21/2002	LOW-K DIELECTRIC STRUCTURE AND METHOD	KLOSTER, GRANT M.
<a href="#"><u>10301956</u></a>	Not Issued	041	11/21/2002	AIR GAP INTERCONNECT STRUCTURE AND METHOD	KLOSTER, GRANT M.
<a href="#"><u>10300378</u></a>	6682989	150	11/20/2002	PLATING A CONDUCTIVE MATERIAL ON A DIELECTRIC MATERIAL	KLOSTER, GRANT
<a href="#"><u>10284722</u></a>	Not Issued	030	10/31/2002	SELECTIVELY GROWING A POLYMERIC MATERIAL ON A SEMICONDUCTOR SUBSTRATE	KLOSTER, GRANT
<a href="#"><u>10259047</u></a>	Not Issued	041	09/26/2002	CREATING AIR GAP IN MULTI-LEVEL METAL INTERCONNECTS USING ELECTRON BEAM TO REMOVE SACRIFICIAL MATERIAL	KLOSTER, GRANT
<a href="#"><u>10252295</u></a>	Not Issued	093	09/23/2002	DIELECTRIC MATERIAL TREATMENT	KLOSTER, GRANT M.
<a href="#"><u>10228539</u></a>	Not Issued	041	08/27/2002	METHOD FOR ALLOY-ELECTROPLATING GROUP IB METALS WITH REFRactory METALS FOR INTERCONNECTIONS	KLOSTER, GRANT M.
<a href="#"><u>10217966</u></a>	Not Issued	041	08/12/2002	LOW-K DIELECTRIC FILM WITH GOOD MECHANICAL STRENGTH	KLOSTER, GRANT
<a href="#"><u>10134264</u></a>	Not Issued	094	04/29/2002	FORMING OPENINGS WITHIN INTEGRATED CIRCUITS	KLOSTER, GRANT M.
<a href="#"><u>10105431</u></a>	Not Issued	041	03/26/2002	METHOD OF MAKING SEMICONDUCTOR DEVICE USING A NOVEL INTERCONNECT CLADDING LAYER	KLOSTER, GRANT
<a href="#"><u>10097328</u></a>	Not	041	03/15/2002	METHOD OF MAKING A	KLOSTER,

	Issued			SEMICONDUCTOR DEVICE USING A DAMASCENE INTERCONNECT WITH A LAMINATED DIELECTRIC	GRANT
<a href="#"><u>09968459</u></a>	Not Issued	061	09/28/2001	DUAL-DAMASCENE INTERCONNECTS WITHOUT AN ETCH-STOP LAYER BY ALTERNATING ILDS	KLOSTER, GRANT M
<a href="#"><u>09968212</u></a>	<a href="#"><u>6605549</u></a>	150	09/29/2001	METHOD FOR IMPROVING NUCLEATION AND ADHESION OF CVD AND ALD FILMS DEPOSITED ONTO LOW-DIELECTRIC-CONSTANT DIELECTRICS	KLOSTER, GRANT
<a href="#"><u>09820079</u></a>	Not Issued	080	03/28/2001	STRUCTURE IN A MICROELECTRONIC DEVICE INCLUDING A BI-LAYER FOR A DIFFUSION BARRIER AND AN ETCH-STOP LAYER	KLOSTER, GRANT

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